

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
3 February 2005 (03.02.2005)

PCT

(10) International Publication Number
WO 2005/011016 A3

(51) International Patent Classification⁷: **H01L 51/40**

(21) International Application Number:
PCT/US2004/023375

(22) International Filing Date: 22 July 2004 (22.07.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
60/489,330 22 July 2003 (22.07.2003) US
60/501,687 10 September 2003 (10.09.2003) US

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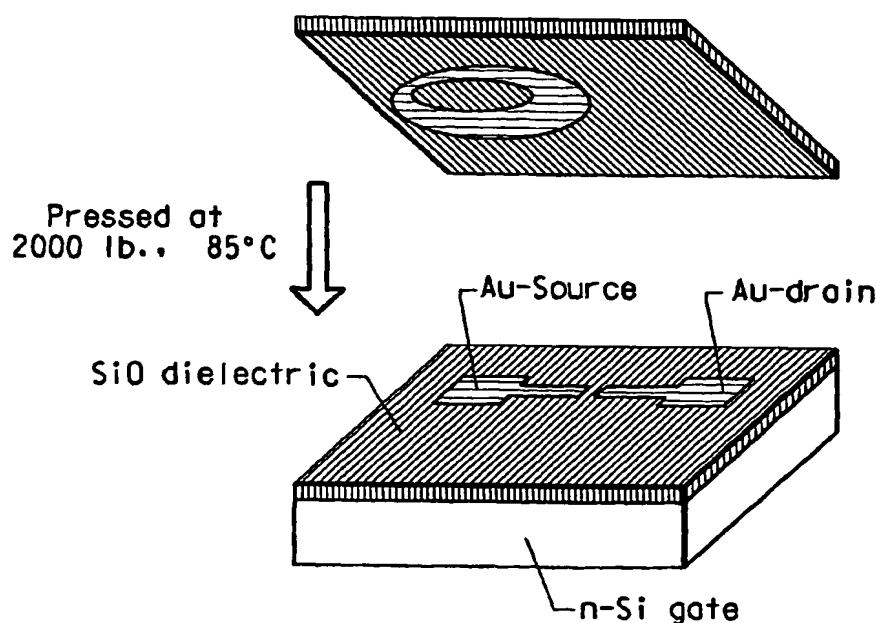
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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, SD, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,

[Continued on next page]

(54) Title: LAMINATION OF ORGANIC SEMICONDUCTORS



(57) Abstract: Low temperature, ambient pressure processes are desired for fabrication of transistors on flexible polymer substrates. Lamination of semiconductors is such a process. The semiconductor is deposited on a donor substrate. The donor is positioned over a receiver substrate, which may be patterned with additional transistor elements. The semiconductor is transferred from the donor to the receiver by lamination.

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SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

Published:

- *with international search report*
- *before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments*

(88) Date of publication of the international search report:

3 March 2005